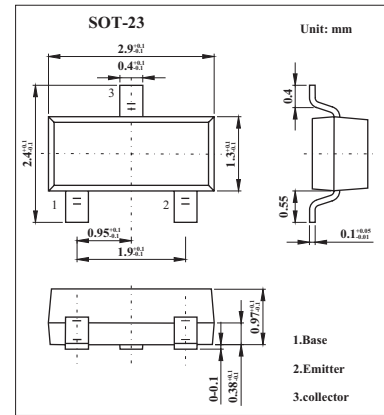


Medium Power Transistor

FMMT491A

■ Features

- Very Low Equivalent Resistance,
- SOT23 NPN Rsilicon planar



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	5	V
Peak collector current	I _{CM}	1	A
Collector current	I _C	2	A
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA	40			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =10mA	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA	5			V
Collector cutoff current	I _{CBO}	V _{CB} =30V, V _{CE} =30V			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V			100	nA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =500mA, I _B =50mA I _C =1A, I _B =100mA			0.3 0.50	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =1A, I _B =100mA			1.1	V
Base-emitter voltage *	V _{BE(ON)}	I _C =1A, V _{CE} =5V			1.0	V
Static Forward Current Transfer Ratio *	h _{FE}	I _C =1mA, V _{CE} =5V	300			
		I _C =500mA, V _{CE} =5V	300		900	
		I _C =1A, V _{CE} =5V	200			
		I _C =2A, V _{CE} =5V	35			
Current-gain-bandwidth product	f _T	I _C =50mA, V _{CE} =10V, f=100MHz	150			MHz
Output capacitance	C _{obo}	V _{CB} =10V, f=1MHz			10	pF

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	41A
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